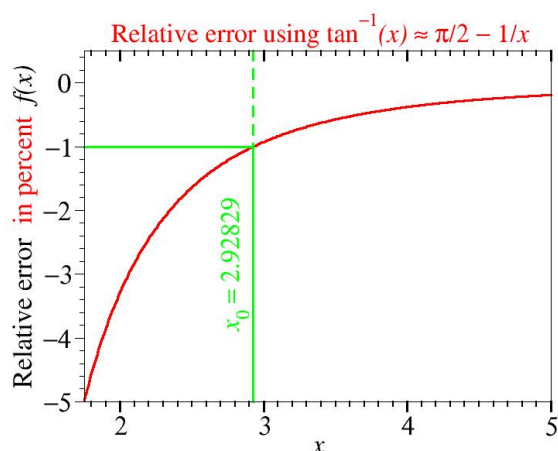


## Supplementary Information

### Can room temperature data for tunneling molecular junctions be analyzed within a theoretical framework assuming zero temperature?

Ioan Bâldea <sup>a\*</sup>

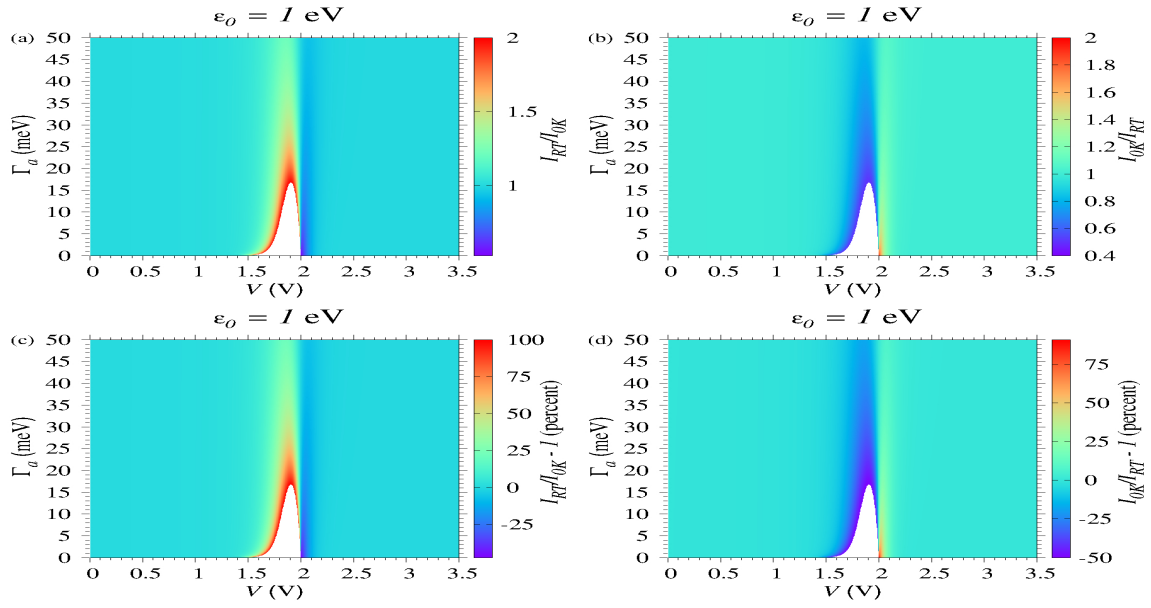
**Keywords:** molecular electronics, nanojunctions, single level model, thermal effects



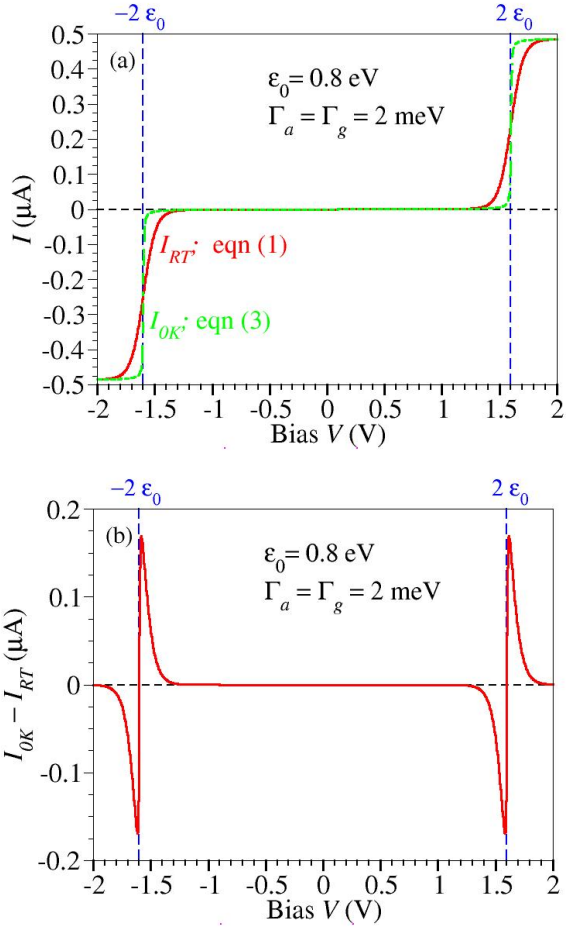
**Fig. S1** Function  $f(x) \equiv 100[(\pi/2 - 1/x)/\tan^{-1}x - 1]$  visualizing that the relative error in percent implied by using eqn (8a) is negligible.

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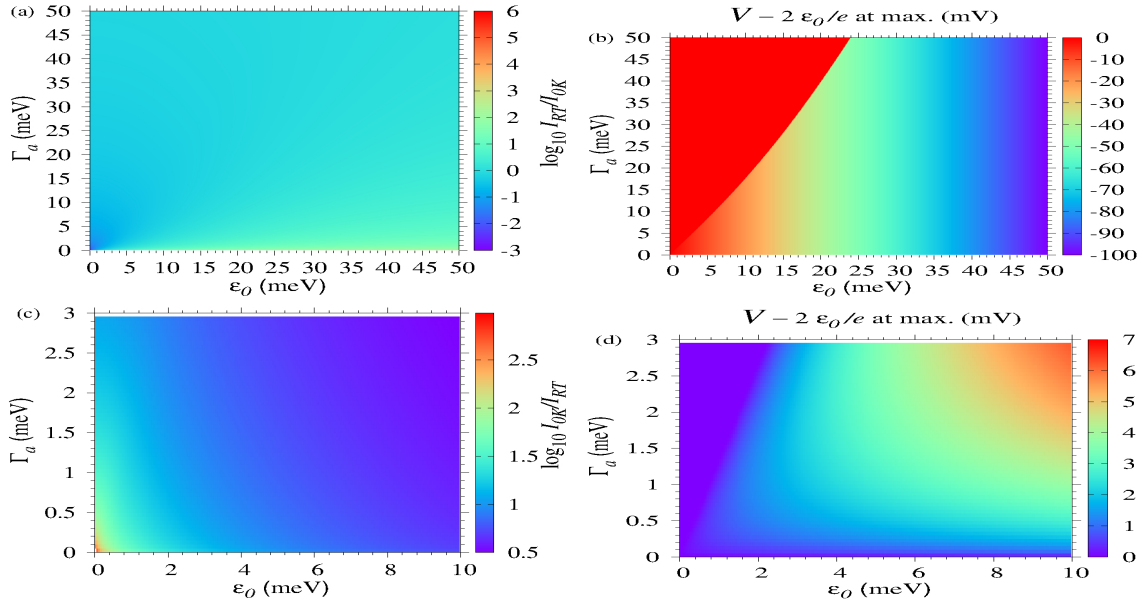
\* E-mail: ioan.baldea@pci.uni-heidelberg.de



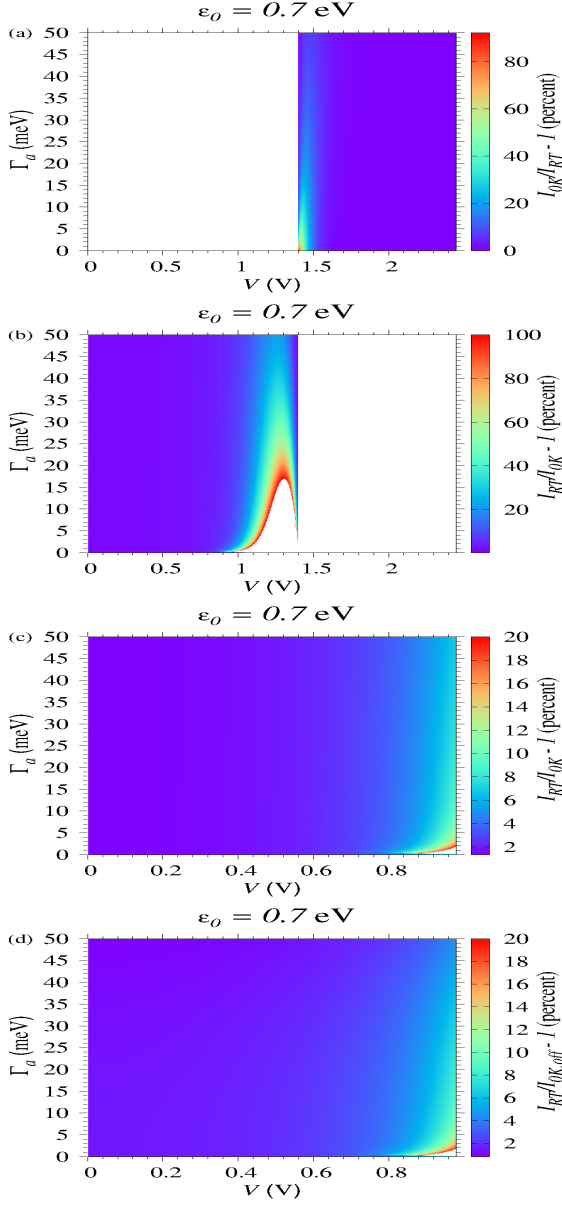
**Fig. S2** Basically, the information presented in this figure on the deviations of the current  $I_{0K}$  computed at zero temperature using eqn (3) from the room temperature  $I_{RT}$  computed via eqn (1) is the same as that of Fig. 1a and b. We prefer the latter manner of presentation because we find it is easier to understand.



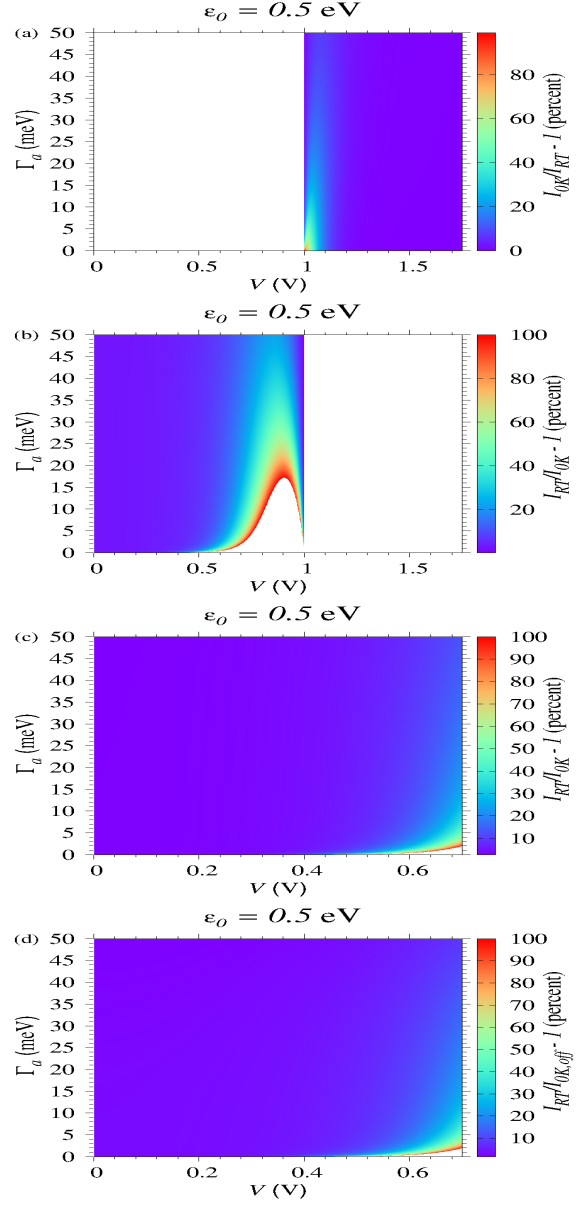
**Fig. S3** (a)  $I$ - $V$  curves computed using eqn (1) and eqn (3) illustrating that the thermal effect (b) enhances the current below resonance ( $|I_{RT}| > |I_{0K}|$  for  $|eV| < 2|\varepsilon_0|$ ) while reducing it above resonance ( $|I_{RT}| < |I_{0K}|$  for  $|eV| > 2|\varepsilon_0|$ ).



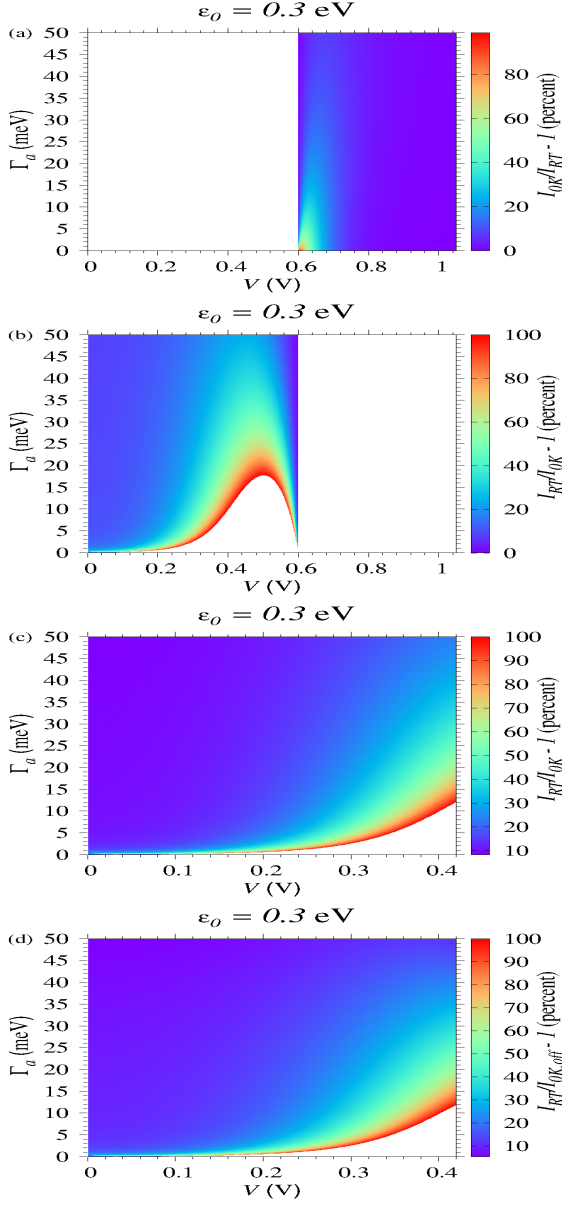
**Fig. S4** Results at very small values of the MO offset  $\epsilon_0$  showing an opposite behavior to that at (reasonably) large  $\epsilon_0$ . Panel (a) depicts situations below resonance wherein  $I_{RT} < I_{0K}$ . Likewise, panel c shows situations above resonance wherein  $I_{0K} < I_{RT}$ . The values of panel a (panel c) were computed at the biases  $V_m$  that maximize the ratio  $I_{RT}/I_{0K}$  ( $I_{0K}/I_{RT}$ ). The corresponding differences from resonance  $V_m - 2\epsilon_0/e$  are presented in panels b and d, respectively.



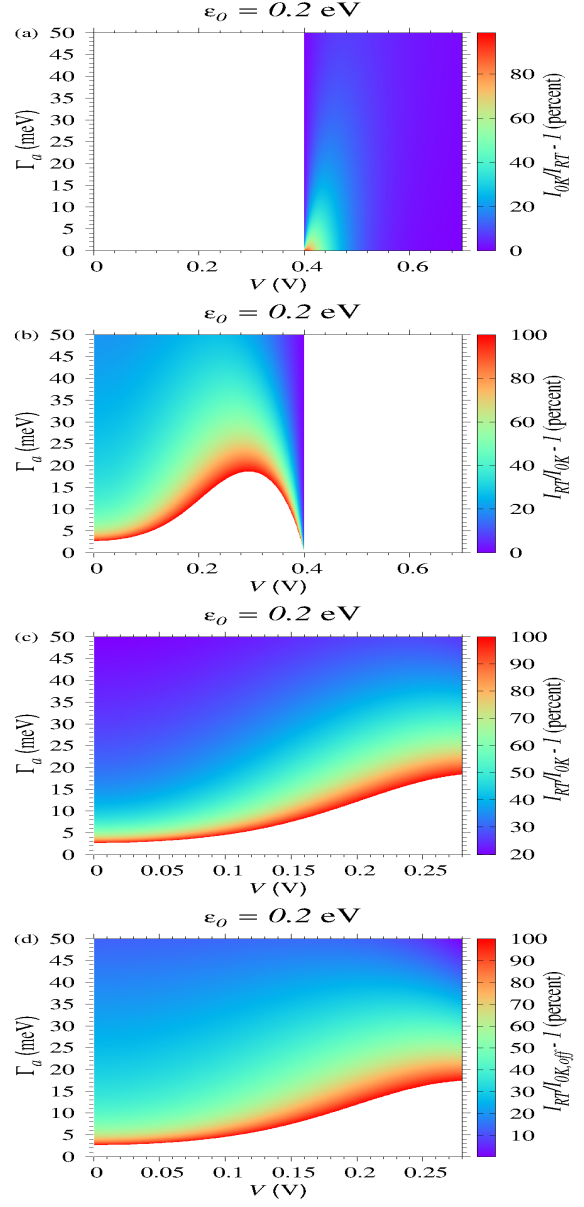
**Fig. S5** The colored regions in the plane  $(V, \Gamma_d)$  depict situations where, at the fixed value of the MO energy offset indicated ( $\varepsilon_0 = 0.7$  eV), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\varepsilon_0|$ , panel a) or smaller ( $|eV| < 2|\varepsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). For parameter values compatible with eqn (10) and (11), the current  $I_{0K,off}$  computed using eqn (9) is very accurate (panel d); it is as accurate as  $I_{0K}$  (panel c). Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



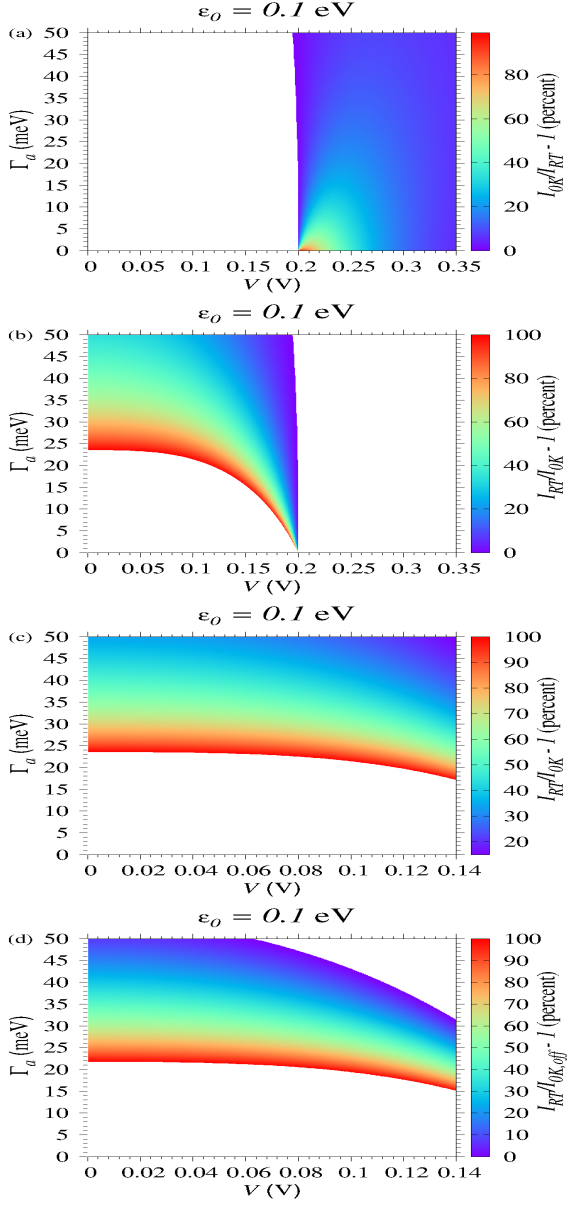
**Fig. S6** The colored regions in the plane  $(V, \Gamma_d)$  depict situations where, at the fixed value of the MO energy offset indicated ( $\varepsilon_0 = 0.5$  eV), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\varepsilon_0|$ , panel a) or smaller ( $|eV| < 2|\varepsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). For parameter values compatible with eqn (10) and (11), the current  $I_{0K,off}$  computed using eqn (9) is very accurate (panel d); it is as accurate as  $I_{0K}$  (panel c). Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



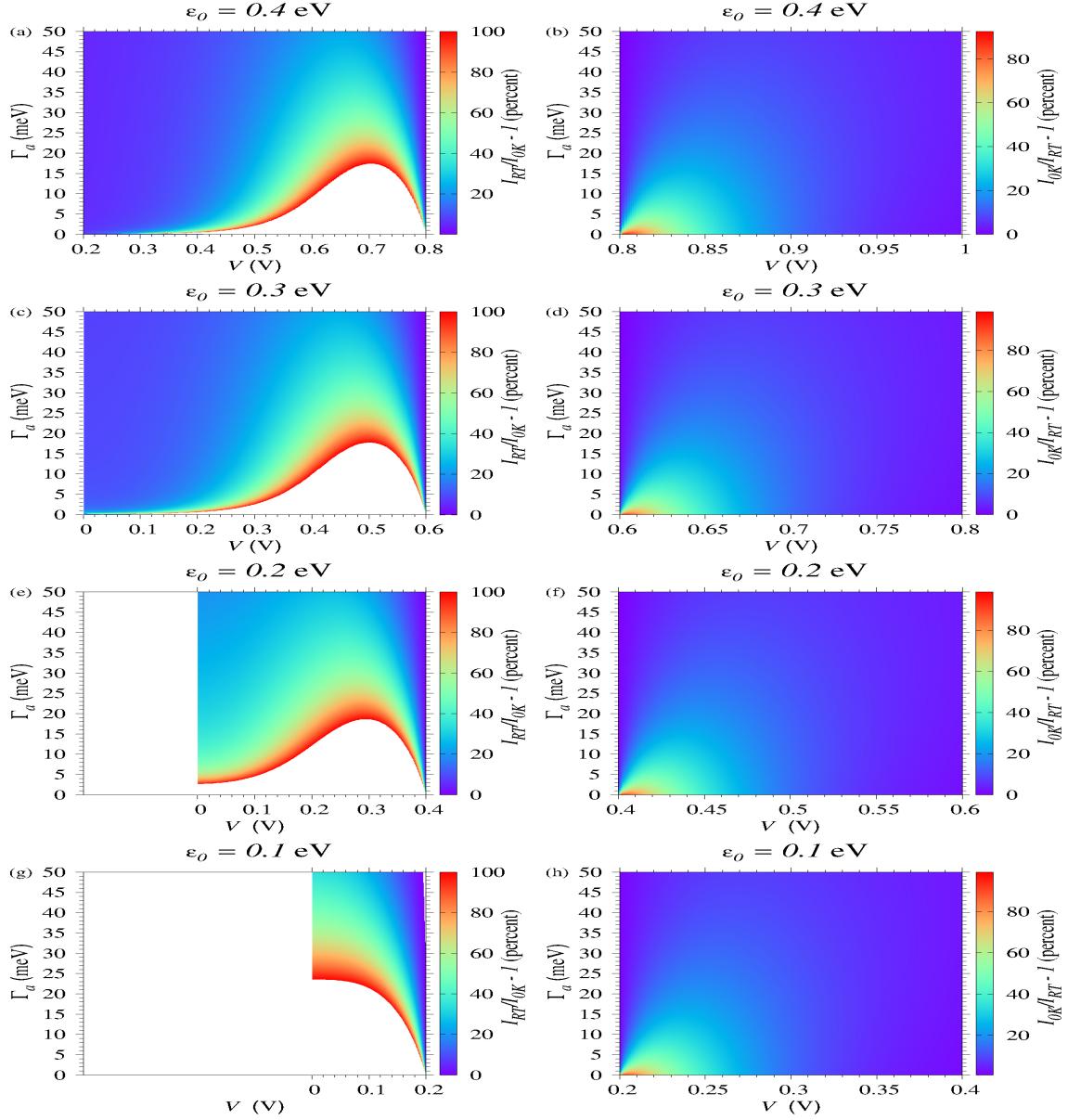
**Fig. S7** The colored regions in the plane  $(V, \Gamma_d)$  depict situations where, at the fixed value of the MO energy offset indicated ( $\epsilon_0 = 0.3$  eV), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\epsilon_0|$ , panel a) or smaller ( $|eV| < 2|\epsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). For parameter values compatible with eqn (10) and (11), the current  $I_{0K,off}$  computed using eqn (9) (panel d) is as accurate as  $I_{0K}$  (panel c). Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



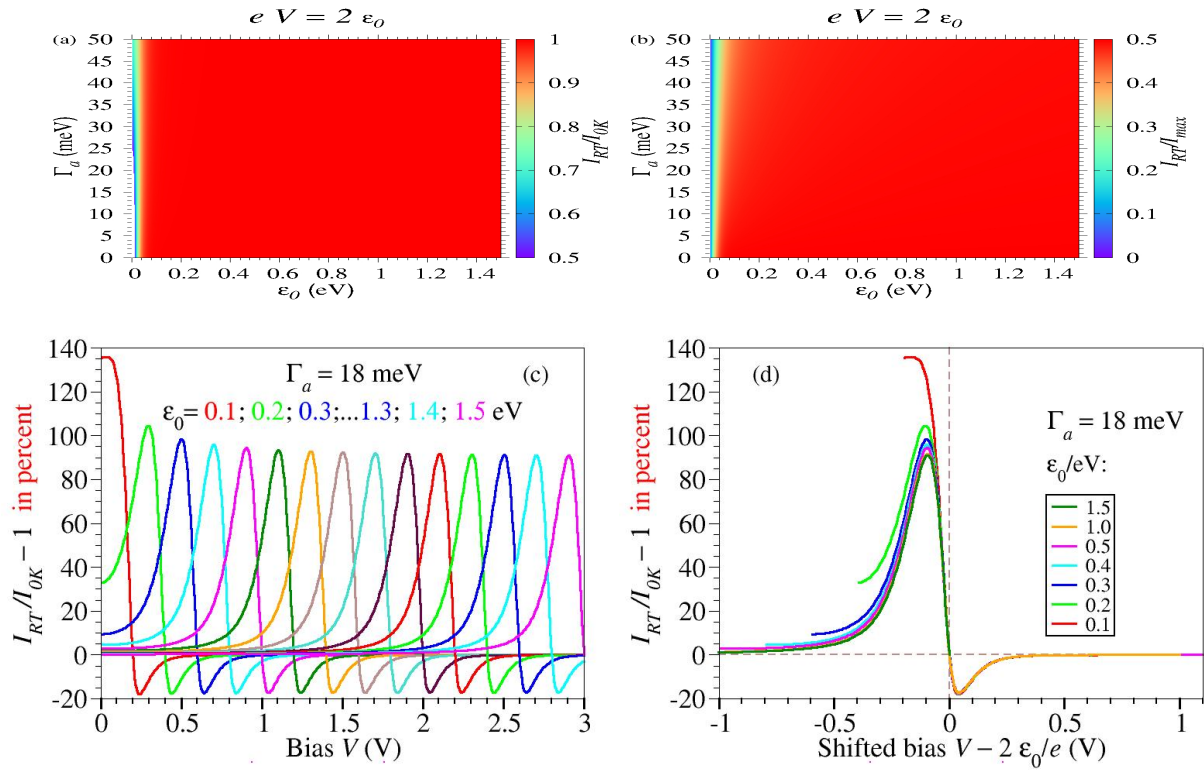
**Fig. S8** The colored regions in the plane  $(V, \Gamma_d)$  depict situations where, at the fixed value of the MO energy offset indicated ( $\epsilon_0 = 0.2$  eV), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\epsilon_0|$ , panel a) or smaller ( $|eV| < 2|\epsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). For parameter values compatible with eqn (10) and (11), the current  $I_{0K,off}$  computed using eqn (9) (panel d) is as accurate as  $I_{0K}$  (panel c). Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



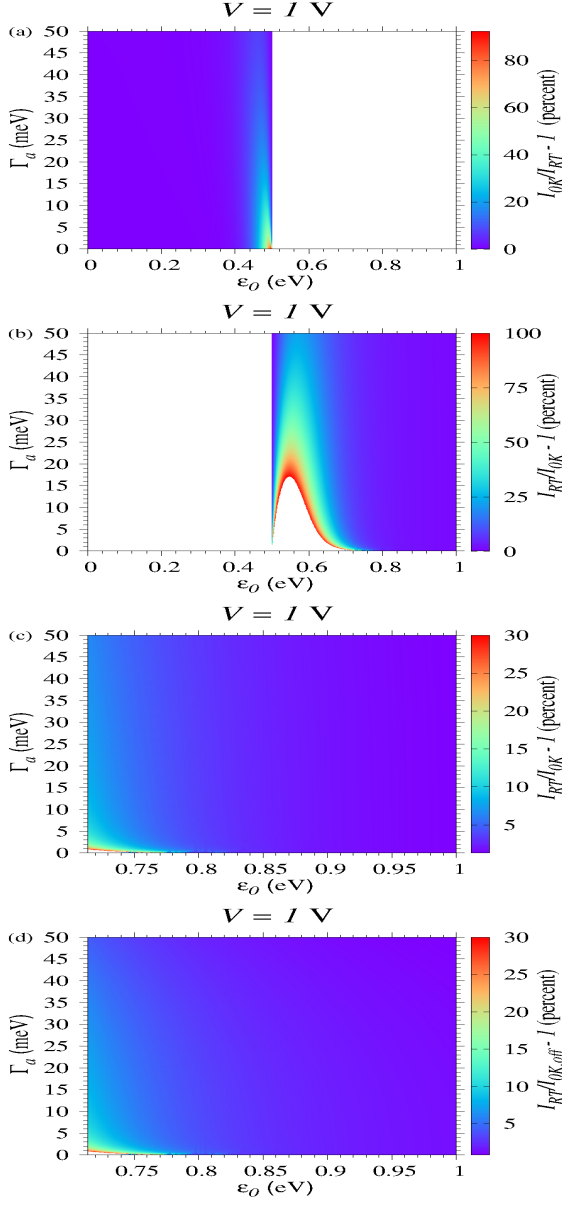
**Fig. S9** The colored regions in the plane  $(V, \Gamma_a)$  depict situations where, at the fixed value of the MO energy offset indicated ( $\varepsilon_0 = 0.1$  eV), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\varepsilon_0|$ , panel a) or smaller ( $|eV| < 2|\varepsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). For situations violating eqn (11), the current  $I_{0K,off}$  computed using eqn (9) (panel d) stronger departs from  $I_{RT}$  than  $I_{0K}$  (panel d). Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



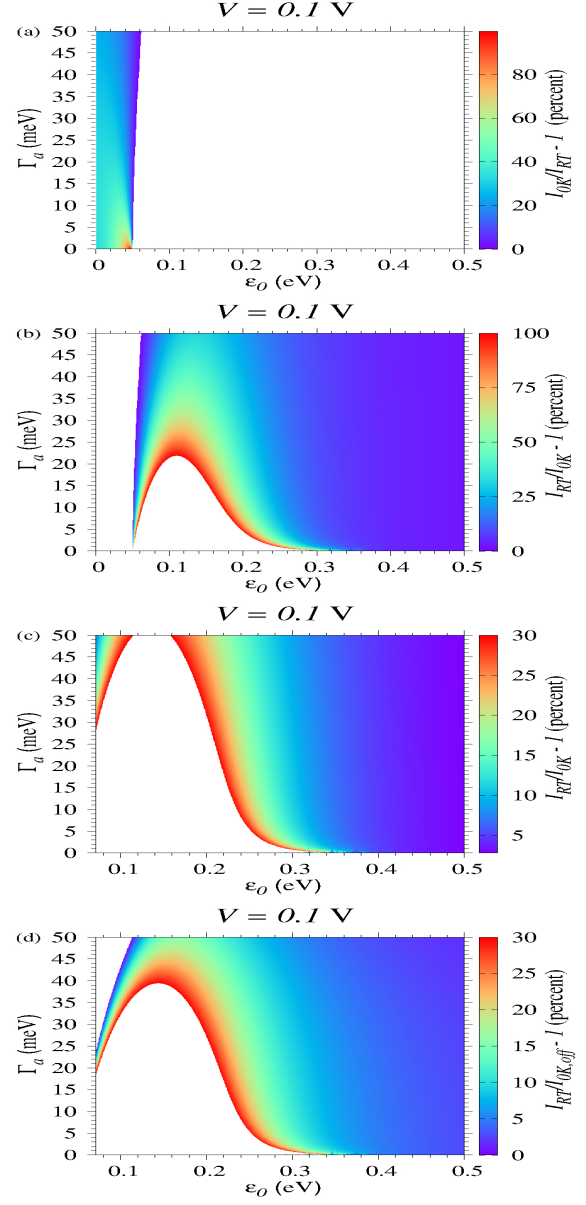
**Fig. S10** Results for lower biases illustrating the current enhancement below resonance ( $|eV| < 2|\varepsilon_0|$ , left panels) and current reduction above resonance ( $|eV| > 2|\varepsilon_0|$ , right panels). As  $\varepsilon_0$  decreases (downwards), the white (empty) region (wherein the relative deviations exceed 100%) in the left panels extends upwards to larger  $\Gamma_a$  and comprises a broader bias range. Notice that all rightmost (leftmost) positions of the left (right) panels are aligned to resonance.



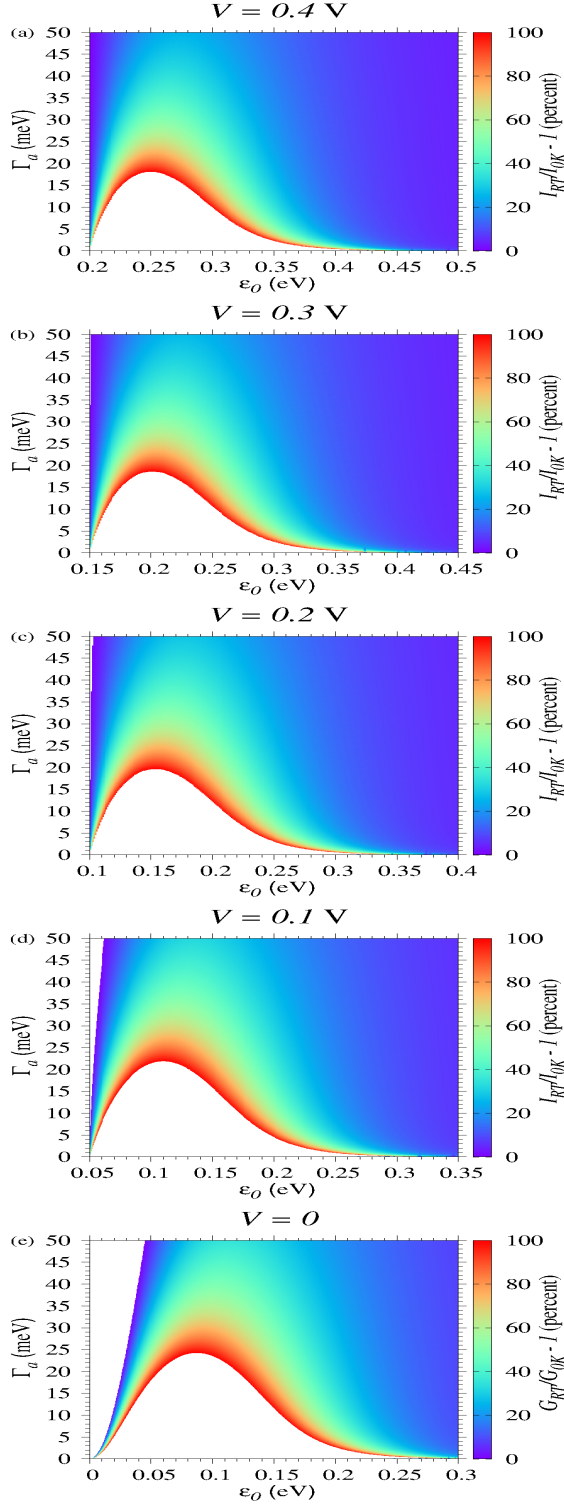
**Fig. S11** (a,b) Strictly on resonance, the temperature impact on the current is negligible. (c,d) Except for small values of the MO energy offset  $\epsilon_0$ , the thermal enhancement of the current occurs around resonance and is quite insensitive to  $\epsilon_0$ .



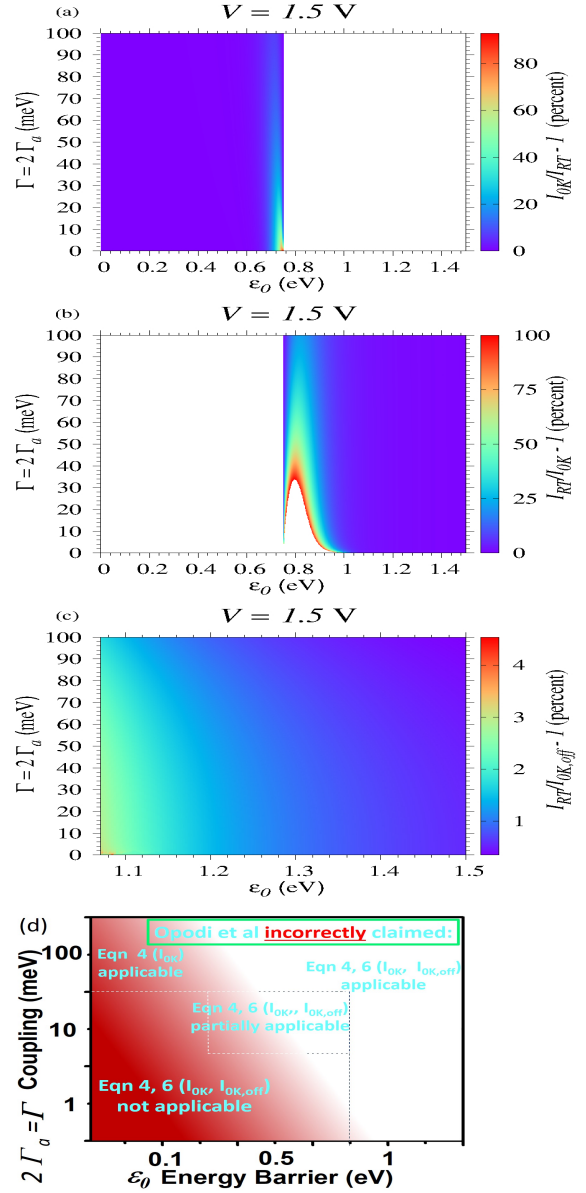
**Fig. S12** The colored regions in the plane  $(\epsilon_0, \Gamma_a)$  depict situations where, at the fixed bias indicated ( $V = 1$  V), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\epsilon_0|$ , panel a) or smaller ( $|eV| < 2|\epsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). For parameter values compatible with eqn (10) and (11), the current  $I_{0K,off}$  computed using eqn (9) is very accurate (panel d); it is as accurate as  $I_{0K}$  (panel c). Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



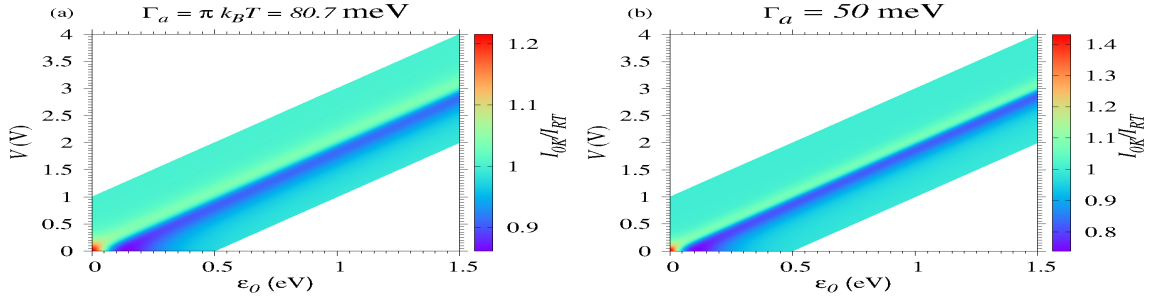
**Fig. S13** The colored regions in the plane  $(\epsilon_0, \Gamma_a)$  depict situations where, at the fixed bias indicated ( $V = 0.1$  V), the current  $I_{0K}$  computed at  $T = 0$  using eqn (3) is larger ( $|eV| > 2|\epsilon_0|$ , panel a) or smaller ( $|eV| < 2|\epsilon_0|$ , panel b) than the exact current  $I_{RT}$  computed from eqn (1) at room temperature ( $T = 298.15$  K). The fact that in this case, paradoxically, the current  $I_{0K,off}$  computed using eqn (9) (panel d) is closer to  $I_{RT}$  than  $I_{0K}$  (panel c) is an error compensation effect. Relative deviations (shown only when not exceeding 100%) are indicated in the color box. To facilitate comparison between  $I_{0K,off}$  and  $I_{0K}$ , abscissas in panel c depicting  $I_{0K}$  are restricted to those in panel d. Notice that the  $z$ -range in panels (c) and (d) is different from panel b.



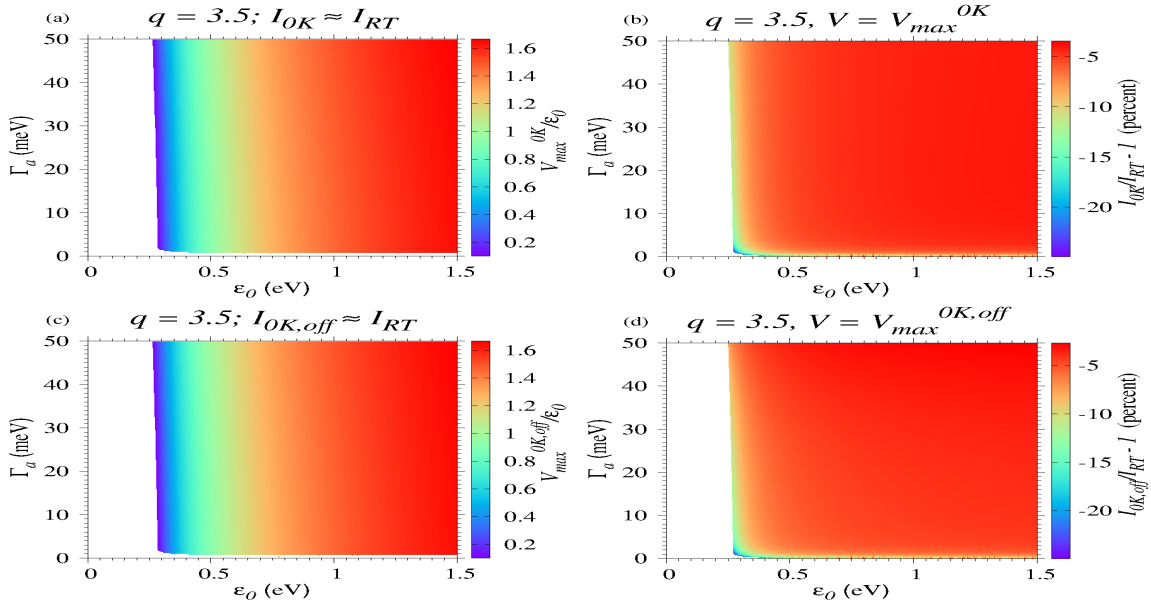
**Fig. S14** Results illustrating the current enhancement below resonance ( $|eV| < 2|\epsilon_0|$ ) at lower biases. As the bias decreases (downwards), the white (empty) region (wherein the relative deviations exceed 100%) extends upwards to larger  $\Gamma_a$  and comprises a broader  $\epsilon_0$ -range. Notice that the leftmost positions of all panels are aligned to resonance.



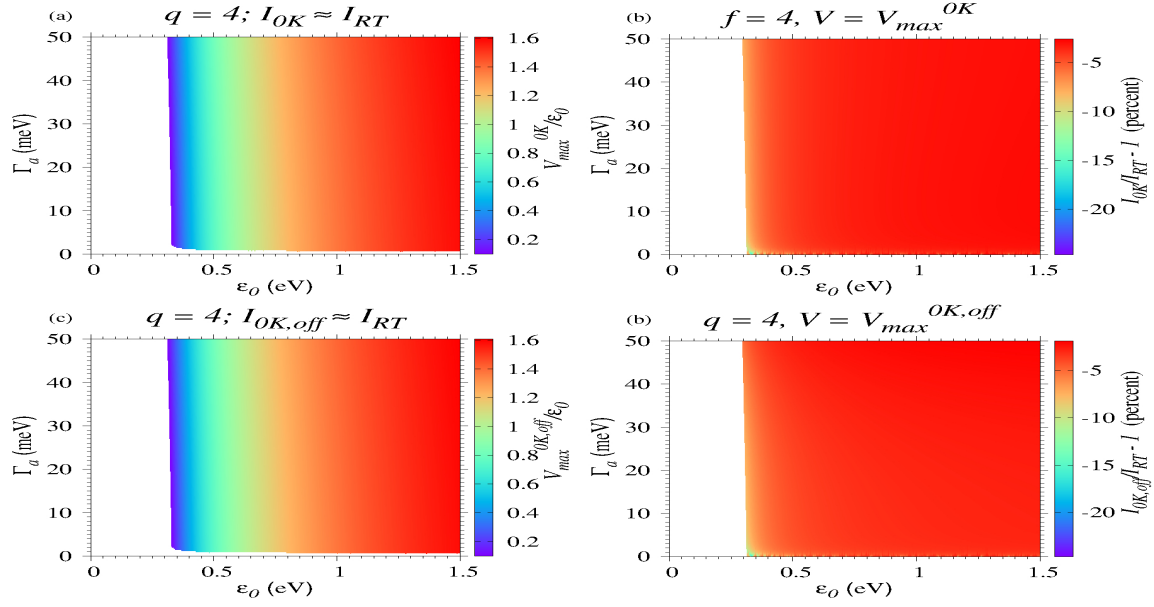
**Fig. S15** Relative deviations in percent of the currents  $I_{0K}$  (panel a and b) and  $I_{0K,off}$  (panel c) computed via eqn (3) and (9) assuming zero temperature from the exact current  $I_{RT}$  computed at room temperature. Comparison with panel d (adapted from Opodi et al, Phys. Chem. Chem. Phys. 2022, 24, 11958 and ref. 26) demonstrates that Fig. 5 of Opodi et al is a factual error. Notice that, in order to facilitate comparison with the paper by Opodi et al, the electronic coupling  $\Gamma = 2\Gamma_a$  in panel d is different from Fig. 4.



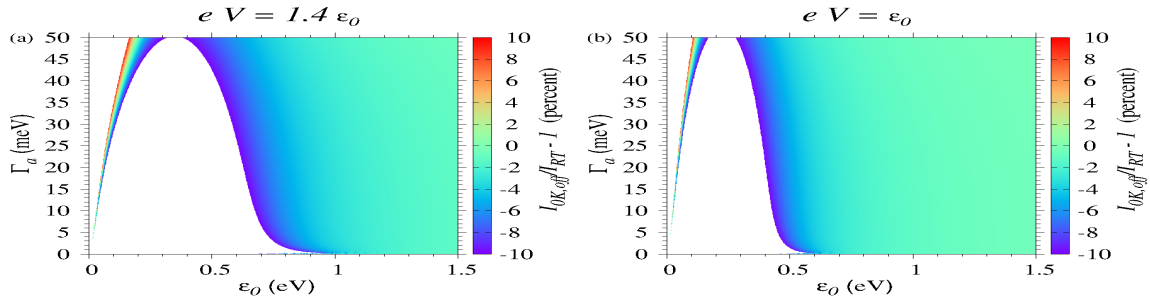
**Fig. S16** Panel b visualizes the weak impact of the (room) temperature on the current at the highest value  $\Gamma_a = 50 \text{ meV}$  chosen in most diagrams, which is even smaller than the value  $\Gamma_a = \pi k_B T_{RT} = 80.7 \text{ meV}$  (panel a) where a weak temperature effect can be expected in view of eqn (13a).



**Fig. S17** Similar to Fig. 9 but setting  $q = 3.5$  in eqn (13b).



**Fig. S18** Similar to Fig. 9 but setting  $q = 4$  in eqn (13b).



**Fig. S19** This figure illustrates how restriction to the narrower bias range  $|eV| < |\epsilon_0|$  (panel b) can render data fitting using  $I_{OK,off}$  (eqn (9)) applicable for junctions having, e.g.,  $\epsilon_0 \simeq 0.5$  eV, a fact impossible when using the broader bias range  $|eV| < 1.4 |\epsilon_0|$  (panel a).